

SSCN3904GS9

NPN Switching Transistor

Features

VCB	VCE	VBE	VCESAT	IC
60V	40V	6V	300mV	200mA

Description

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-723 package, which is designed for telephony and professional communication equipment.

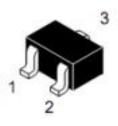
Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

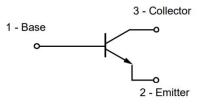
> Ordering Information

Device	Package	Shipping
SSCN3904GS9	SOT-723	8000/Reel

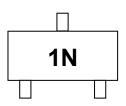
Pin configuration



SOT-723



Circuit Diagram



Marking(Top View)



2/5



ightarrow Absolute Maximum Ratings(T_A=25°C unless otherwise noted)

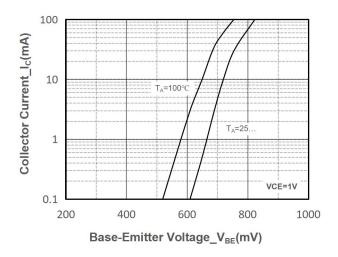
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector- Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	Ic	200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

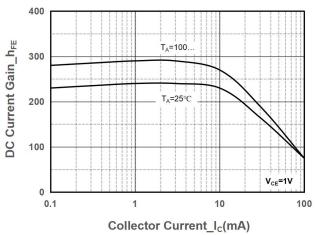
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =10uA,I _E =0	60			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA,I _B =0	40			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =10uA,I _C =0	6			V
Collector Cutoff Current	I _{CEX}	V _{CE} =30V, V _{EB} =3V			50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} =30V,I _E =0			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =3V,I _C =0			100	nA
		V _{CE} =1V,I _C =10mA	100		300	
DC Current Gain	h _{FE}	V _{CE} =1V,I _C =0.1mA	40			
		V _{CE} =1V,I _C =100mA	30			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =50mA,I _B =5mA			0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =50mA,I _B =5mA			0.95	V
Transition fraguency	f⊤	V _{CE} =20V,I _C =10mA	250			MHz
Transition frequency		f=100MHz				
Dolov Time	t _d	V _{CC} =3V,V _{BE(off)} =-0.5V			35	ns
Delay Time		I _C =10mA,I _{B1} =1mA				
Rise Time	t _r	V _{CC} =3V,V _{BE(off)} =-0.5V			35	ns
Rise Tillie		I _C =10mA,I _{B1} =1mA				
Storago Timo	ts	V _{CC} =3V,I _C =10mA			200	ns
Storage Time		I _{B1} = I _{B2} =1mA				
Fall Time	4.	V _{CC} =3V,I _C =10mA			50	ns
raii iiiie	t _f	I _{B1} = I _{B2} =1mA				

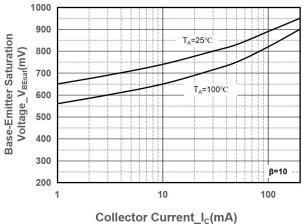


Typical Performance Characteristics (T_A =25 $^{\circ}$ C unless otherwise noted)

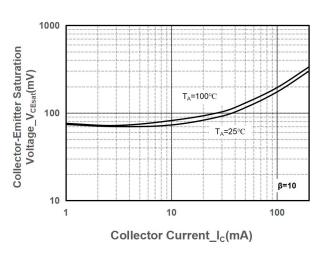




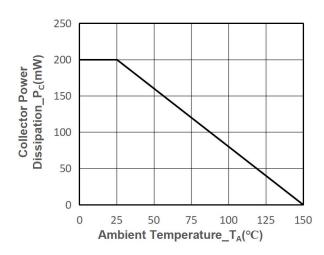
Collector Current vs. Base-Emitter Voltage



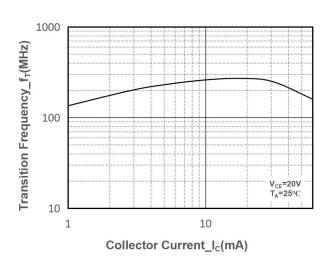
DC Current Gain vs. Collector Current



V_{BE(sat)} vs. Collector Current



V_{CE(sat)} vs. Collector Current



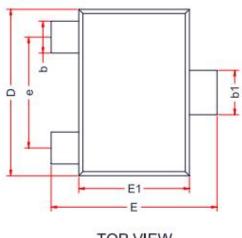
Power derating vs. Ambient temperature

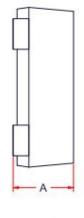
Transition Frequency vs. Collector Current



Package Information

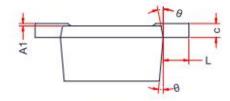
SOT-723





TOP VIEW

SIDE VIEW



SIDE VIEW

DIM	Millimeters			
	Min.	Тур.	Max.	
Α	0.43	-	0.55	
A1	0.00	-	0.05	
b1	0.27		0.37	
b	0.17	-	0.27	
С	0.08	0.13	0.18	
D	1.15	1.20	1.25	
E	1.15	1.20	1.25	
E1	0.75	0.8	0.85	
е	0.80Ref.			
L1	0.15	0.2	0.25	
θ	7°Ref.			



DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G,. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.